Please amend Claim 34, as follows:

34. (Twice Amended) A semiconductor device, comprising:

a substrate;

a gate electrode provided on said substrate;

a diffusion region formed in said substrate adjacent to said gate electrode;

a side-wall insulation film formed on side wall of said gate electrode; [and]

a self-aligned contact hole defined by said side-wall oxide film and exposing said diffusion region; and

a silicide region formed selectively on a surface of said diffusion region,

wherein said semiconductor device further includes:

a first insulation film provided on said gate electrode so as to cover said side wall oxide film partially;

a second insulation film having a composition different from a composition of said first insulation film and provided on said first insulation film;

an interlayer insulation film deposited on said second insulation film;

a contact hole formed in said interlayer insulation film, said contact hole extending through said first and second insulation films and exposing said self-aligned contact hole;

said first insulation film is formed of PSG containing P with an amount of about 6 wt% or less.

Please amend Claim 41, as follows:

41. (Twice Amended) A semiconductor device as claimed in claim [40] 38, further comprising another silicide region formed selectively on a surface of said gate electrode.

Add new Claim 42, as follows:

42. A method of fabricating a semiconductor device, comprising the steps of:

(A) forming a refractory metal layer on a diffusion region in a semiconductor substrate;

(B) forming a self-aligned silicide layer on said refractory metal layer by applying a heat-treatment process;

(C) forming an insulation film on a surface of said silicide layer by conducting a plasma CVD process while using a source gas containing SiH_4 and N_2O with a ratio of N_2O with respect to SiH_4 equal to or less than 5;

(D) forming a nitride film, after said step (C), on said insulation film in contact with said insulation film, without exposing a surface of said insulation film to the air;

(E) forming an interlayer insulation film so as to cover said nitride film; and

(F) forming a window exposing said silicide layer, by applying a dry etching process consecutively to said interlayer insulation film, said nitride film, and said insulation film.

Cancel Claim 40, without prejudice or disclaimer.